Timothy D Sands

List of Publications by Year
in descending order

222 papers	11,468 citations	26567 56 h-index	33814 99 g-index
227 all docs	227 docs citations	227 times ranked	9041 citing authors

#	Article	IF	Citations
1	Titanium nitride as a plasmonic material for visible and near-infrared wavelengths. Optical Materials Express, 2012, 2, 478.	1.6	567
2	Damage-free separation of GaN thin films from sapphire substrates. Applied Physics Letters, 1998, 72, 599-601.	1.5	410
3	Fatigue and retention in ferroelectric Yâ€Baâ€Cuâ€O/Pbâ€Zrâ€Tiâ€O/Yâ€Baâ€Cuâ€O heterostructures. Applied Physics Letters, 1992, 61, 1537-1539.	1.5	369
4	Ferroelectric Laâ€Srâ€Coâ€O/Pbâ€Zrâ€Tiâ€O/Laâ€Srâ€Coâ€O heterostructures on silicon via template growth. Applied Physics Letters, 1993, 63, 3592-3594.	1.5	351
5	Nanoscale design to enable the revolution in renewable energy. Energy and Environmental Science, 2009, 2, 559.	15.6	348
6	Equilibrium limits of coherency in strained nanowire heterostructures. Journal of Applied Physics, 2005, 97, 114325.	1.1	337
7	Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off. Applied Physics Letters, 1999, 75, 1360-1362.	1.5	326
8	Electrodeposition of Ordered Bi2Te3Nanowire Arrays. Journal of the American Chemical Society, 2001, 123, 7160-7161.	6.6	298
9	Fabrication of High-Density, High Aspect Ratio, Large-Area Bismuth Telluride Nanowire Arrays by Electrodeposition into Porous Anodic Alumina Templates. Advanced Materials, 2002, 14, 665-667.	11.1	284
10	Insights into the Electrodeposition of Bi[sub 2]Te[sub 3]. Journal of the Electrochemical Society, 2002, 149, C546.	1.3	228
11	Epitaxial growth of ferromagnetic ultrathin MnGa films with perpendicular magnetization on GaAs. Applied Physics Letters, 1993, 62, 1565-1567.	1.5	205
12	Epitaxial superlattices with titanium nitride as a plasmonic component for optical hyperbolic metamaterials. Proceedings of the National Academy of Sciences of the United States of America, 2014, 111, 7546-7551.	3.3	198
13	InxGa1â^'xN light emitting diodes on Si substrates fabricated by Pdâ€“In metal bonding and laser lift-off. Applied Physics Letters, 2000, 77, 2822-2824.	1.5	178
14	Structure of Bismuth Telluride Nanowire Arrays Fabricated by Electrodeposition into Porous Anodic Alumina Templates. Chemistry of Materials, 2003, 15, 335-339.	3.2	170
15	Oriented ferroelectric Laâ€Srâ€Coâ€O/Pbâ€Laâ€Zrâ€Tiâ€O/Laâ€Srâ€Coâ€O heterostructures on [001] Pt/SiO2Si substrates using a bismuth titanate template layer. Applied Physics Letters, 1994, 64, 2511-2513.	1.5	152
16	Direct Electrodeposition of Highly Dense 50 nm Bi2Te3-ySeyNanowire Arrays. Nano Letters, 2003, 3, 973-977.	4.5	146
17	High-Density 40 nm Diameter Sb-Rich Bi2xSbxTe3 Nanowire Arrays. Advanced Materials, 2003, 15, 1003-1006.	11.1	137
18	The Electrodeposition of High-Density, Ordered Arrays of Bi1-xSbxNanowires. Journal of the American Chemical Society, 2003, 125, 2388-2389.	6.6	129

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19	Electronic structure, phonons, and thermal properties of ScN, ZrN, and HfN: A first-principles study. Journal of Applied Physics, 2010, 107, .	1.1	125
20	Effects of crystalline quality and electrode material on fatigue in Pb(Zr,Ti)O3thin film capacitors. Applied Physics Letters, 1993, 63, 27-29.	1.5	124
21	Epitaxial ferromagnetic Ï„â€MnAl films on GaAs. Applied Physics Letters, 1990, 57, 2609-2611.	1.5	116
22	Heterogeneous integration of CdS filters with GaN LEDs for fluorescence detection microsystems. Sensors and Actuators A: Physical, 2004, 111, 1-7.	2.0	115
23	Thermal conductivity of (Zr,W)N/ScN metal/semiconductor multilayers and superlattices. Journal of Applied Physics, 2009, 105, .	1.1	114
24	Dislocation Filtering in GaN Nanostructures. Nano Letters, 2010, 10, 1568-1573.	4.5	110
25	Ferroelectric PbZr0.2Ti0.8O3thin films on epitaxial Yâ€Baâ€Cuâ€O. Applied Physics Letters, 1991, 59, 3542-3544.	1.5	108
26	Solid-phase regrowth of compound semiconductors by reaction-driven decomposition of intermediate phases. Journal of Materials Research, 1988, 3, 914-921.	1.2	107
27	A comparative study of phase stability and film morphology in thinâ€film M/GaAs systems (M=Co, Rh, Ir,) Tj ETQq1 1 0.784314 rgBT /Ov	1.1	106
28	Structure and composition of NixGaAs. Applied Physics Letters, 1986, 48, 402-404.	1.5	99
29	Faceted and Vertically Aligned GaN Nanorod Arrays Fabricated without Catalysts or Lithography. Nano Letters, 2005, 5, 1847-1851.	4.5	98
30	Stability and epitaxy of NiAl and related intermetallic films on IIIâ€V compound semiconductors. Applied Physics Letters, 1988, 52, 197-199.	1.5	96
31	Molecular beam epitaxial growth of ultrathin buried metal layers: (Al,Ga)As/NiAl/(Al,Ga)As heterostructures. Applied Physics Letters, 1988, 53, 1717-1719.	1.5	93
32	Thermoelectric properties of epitaxial ScN films deposited by reactive magnetron sputtering onto MgO(001) substrates. Journal of Applied Physics, 2013, 113, .	1.1	91
33	Van der Waals bonding of GaAs on Pd leads to a permanent, solidâ€phaseâ€topotaxial, metallurgical bond. Applied Physics Letters, 1991, 59, 3159-3161.	1.5	90
34	Effect of crystallographic orientation on ferroelectric properties of PbZr0.2Ti0.8O3thin films. Applied Physics Letters, 1993, 63, 731-733.	1.5	89
35	Reduction of the energy gap pressure coefficient of GaN due to the constraining presence of the sapphire substrate. Journal of Applied Physics, 1999, 85, 2385-2389.	1.1	87
36	Laser-driven formation of a high-pressure phase in amorphous silica. Nature Materials, 2003, 2, 796-800.	13.3	86

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37	ErAs epitaxial layers buried in GaAs: Magnetotransport and spin-disorder scattering. Physical Review Letters, 1989, 62, 2309-2312.	2.9	82
38	GaN Nanorod Schottky and pâ”n Junction Diodes. Nano Letters, 2006, 6, 2893-2898.	4.5	79
39	Changing the academic culture: Valuing patents and commercialization toward tenure and career advancement. Proceedings of the National Academy of Sciences of the United States of America, 2014, 111, 6542-6547.	3.3	79
40	Initial stages of the Pd-GaAs reaction: Formation and decomposition of ternary phases. Thin Solid Films, 1986, 136, 105-122.	0.8	78
41	Anisotropic Effects on the Thermoelectric Properties of Highly Oriented Electrodeposited Bi2Te3 Films. Scientific Reports, 2016, 6, 19129.	1.6	76
42	Negative differential resistance in AlAs/NiAl/AlAs heterostructures: Evidence for size quantization in metals. Applied Physics Letters, 1988, 53, 2528-2530.	1.5	73
43	Electrodeposition of Bi1-xSbx Films and 200-nm Wire Arrays from a Nonaqueous Solvent. Chemistry of Materials, 2003, 15, 1676-1681.	3.2	73
44	Thermal properties of electrodeposited bismuth telluride nanowires embedded in amorphous alumina. Applied Physics Letters, 2004, 85, 6001-6003.	1.5	73
45	Thermoelectric Transport in a ZrN/ScN Superlattice. Journal of Electronic Materials, 2009, 38, 960-963.	1.0	71
46	An investigation of a nonspiking Ohmic contact to n-GaAs using the Si/Pd system. Journal of Materials Research, 1988, 3, 922-930.	1.2	68
47	Epitaxial growth of GaAs/NiAl/GaAs heterostructures. Applied Physics Letters, 1988, 52, 1216-1218.	1.5	66
48	Cross-plane thermal conductivity of (Ti,W)N/(Al,Sc)N metal/semiconductor superlattices. Physical Review B, 2016, 93, .	1.1	64
49	The atomic structure of growth interfaces in Yâ€“Baâ€“Cuâ€“O thin films. Journal of Materials Research, 1991, 6, 2264-2271.	1.2	61
50	Dendrimer-assisted controlled growth of carbon nanotubes for enhanced thermal interface conductance. Nanotechnology, 2007, 18, 385303.	1.3	60
51	Thermal conductivity of bismuth telluride nanowire array-epoxy composite. Applied Physics Letters, 2009, 94, .	1.5	60
52	Surface outgrowth problem incâ€axis oriented Yâ€Baâ€Cuâ€O superconducting thin films. Applied Physics Letters, 1991, 58, 1557-1559.	1.5	59
53	Vertical single- and double-walled carbon nanotubes grown from modified porous anodic alumina templates. Nanotechnology, 2006, 17, 3925-3929.	1.3	59
54	Rocksalt nitride metal/semiconductor superlattices: A new class of artificially structured materials. Applied Physics Reviews, 2018, 5, 021101.	5.5	59

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55	Epitaxial CoGa and textured CoAs contacts on Ga1â^'xAlxAs fabricated by molecularâ€beam epitaxy. Journal of Applied Physics, 1989, 65, 4753-4758.	1.1	58
56	Ferroelectric bismuth titanate/superconductor (Yâ€Baâ€Cuâ€O) thinâ€film heterostructures on silicon. Applied Physics Letters, 1991, 59, 1782-1784.	1.5	58
57	Microstructure of epitaxial La0.5Sr0.5CoO3/ferroelectric Pb0.9La0.1(Zr0.2Ti0.8)0.975O3/La0.5Sr0.5CoO3heterostructures on LaAlO3. Applied Physics Letters, 1993, 63, 1628-1630.	1.5	58
58	Compound semiconductor contact metallurgy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1988, 1, 289-312.	1.7	57
59	Stable and shallow PdIn ohmic contacts tonâ€GaAs. Applied Physics Letters, 1990, 56, 2129-2131.	1.5	57
60	Structural and optical quality of GaN/metal/Si heterostructures fabricated by excimer laser lift-off. Applied Physics Letters, 1999, 75, 1887-1889.	1.5	57
61	Dislocation-pipe diffusion in nitride superlattices observed in direct atomic resolution. Scientific Reports, 2017, 7, 46092.	1.6	57
62	Compensation of native donor doping in ScN: Carrier concentration control and p-type ScN. Applied Physics Letters, 2017, 110, .	1.5	57
63	Phase formation in the Pdâ€InP system. Journal of Applied Physics, 1988, 64, 4909-4913.	1.1	54
64	Scaling of ferroelectric properties in Laâ€Srâ€Coâ€O/Pbâ€Laâ€Zrâ€Tiâ€O/Laâ€Srâ€Coâ€O capacitors. Applied Physics Letters, 1994, 64, 1588-1590.	1.5	54
65	Integration of GaN thin films with dissimilar substrate materials by Pd-In metal bonding and laser lift-off. Journal of Electronic Materials, 1999, 28, 1409-1413.	1.0	54
66	Niâ€InP reaction: Formation of amorphous and crystalline ternary phases. Applied Physics Letters, 1987, 50, 1346-1348.	1.5	53
67	Structural and chemical characterization of free-standing GaN films separated from sapphire substrates by laser lift-off. Applied Physics Letters, 2000, 77, 1819.	1.5	53
68	Epitaxial ferroelectric thin films for memory applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 22, 283-289.	1.7	52
69	Epitaxial ferroelectric (Pb,â€ŠLa)(Zr,â€ŠTi)O3 thin films on stainless steel by excimer laser liftoff. Applied Physics Letters, 2000, 76, 227-229.	1.5	52
70	TiN/(Al,Sc)N metal/dielectric superlattices and multilayers as hyperbolic metamaterials in the visible spectral range. Physical Review B, 2014, 90, .	1.1	52
71	Nearâ€surface defects formed during rapid thermal annealing of preamorphized and BF+2â€implanted silicon. Applied Physics Letters, 1984, 45, 982-984.	1.5	51
72	High resolution transmission electron microscopy study of Se+â€implanted and annealed GaAs: Mechanisms of amorphization and recrystallization. Applied Physics Letters, 1984, 44, 623-625.	1.5	51

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73	Electroâ€optic properties of single crystalline ferroelectric thin films. Applied Physics Letters, 1993, 63, 596-598.	1.5	51
74	NiAl/nâ€GaAs Schottky diodes: Barrier height enhancement by highâ€temperature annealing. Applied Physics Letters, 1988, 52, 1338-1340.	1.5	49
75	Galvanomagnetic properties of epitaxial MnAl films on GaAs. Journal of Applied Physics, 1991, 69, 4689-4691.	1.1	49
76	Electronic structure, vibrational spectrum, and thermal properties of yttrium nitride: A first-principles study. Journal of Applied Physics, 2011, 109, 073720.	1.1	49
77	Electronic and optical properties of ScN and (Sc,Mn)N thin films deposited by reactive DC-magnetron sputtering. Journal of Applied Physics, 2013, 114, .	1.1	49
78	An investigation of the Pdâ€Inâ€Ge nonspiking Ohmic contact tonâ€GaAs using transmission line measurement, Kelvin, and Cox and Strack structures. Journal of Applied Physics, 1991, 69, 4364-4372.	1.1	47
79	Machining of transparent materials using an IR and UV nanosecond pulsed laser. Applied Physics A: Materials Science and Processing, 2000, 71, 601-608.	1.1	47
80	Thermal conductivity of skutterudite thin films and superlattices. Applied Physics Letters, 2000, 77, 3854-3856.	1.5	46
81	Development of epitaxial Al_x Sc_{1â^'x} N for artificially structured metal/semiconductor superlattice metamaterials. Physica Status Solidi (B): Basic Research, 2015, 252, 251-259.	0.7	46
82	High Resolution Observations of Copper Vacancy Ordering in Chalcocite (Cu2S) and the Transformation to Djurleite (Cu1.97 to 1.94S). Physica Status Solidi A, 1982, 72, 551-559.	1.7	43
83	Epitaxial MnGa/NiGa magnetic multilayers on GaAs. Applied Physics Letters, 1993, 63, 696-698.	1.5	43
84	Dendrimer-Templated Fe Nanoparticles for the Growth of Single-Wall Carbon Nanotubes by Plasma-Enhanced CVD. Journal of Physical Chemistry B, 2006, 110, 10636-10644.	1.2	43
85	Schottky barrier degradation of the W/GaAs system after highâ€temperature annealing. Journal of Applied Physics, 1986, 60, 3235-3242.	1.1	42
86	Pulsed laser deposition of skutterudite thin films. Journal of Applied Physics, 2001, 89, 3508-3513.	1.1	40
87	MBE growth of ferromagnetic metastable epitaxial MnAl thin films on AlAs/GaAs heterostructures. Journal of Crystal Growth, 1991, 111, 978-983.	0.7	38
88	Phonon wave effects in the thermal transport of epitaxial TiN/(Al,Sc)N metal/semiconductor superlattices. Journal of Applied Physics, 2017, 121, .	1.1	37
89	Template approaches to growth of oriented oxide heterostructures on SiO2/Si. Journal of Electronic Materials, 1994, 23, 19-23.	1.0	36
90	Energy deposition at front and rear surfaces during picosecond laser interaction with fused silica. Applied Physics Letters, 2001, 78, 2840-2842.	1.5	36

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91	Highly ordered diamond and hybrid triangle-diamond patterns in porous anodic alumina thin films. Applied Physics Letters, 2008, 93, .	1.5	35
92	Temperature-dependent thermal and thermoelectric properties of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>n</mml:mi></mml:math> -type and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math> -type <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">S</mml:mi><mml:msub><mml:mi mathvariant="normal">c</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></r	1.1	35
93	Effect of deposition pressure on the microstructure and thermoelectric properties of epitaxial ScN(001) thin films sputtered onto MgO(001) substrates. Journal of Materials Research, 2015, 30, 626-634.	1.2	34
94	Lithography-Free in Situ Pd Contacts to Templated Single-Walled Carbon Nanotubes. Nano Letters, 2006, 6, 2712-2717.	4.5	31
95	Room temperature device performance of electrodeposited InSb nanowire field effect transistors. Applied Physics Letters, 2011, 98, .	1.5	31
96	Reaction of amorphous Niâ€W and Niâ€Nâ€W films with substrate silicon. Journal of Applied Physics, 1984, 56, 2740-2745.	1.1	30
97	Enhancement of (In,Ga)N light-emitting diode performance by laser liftoff and transfer from sapphire to silicon. IEEE Photonics Technology Letters, 2002, 14, 1400-1402.	1.3	30
98	Dendrimer-assisted low-temperature growth of carbon nanotubes by plasma-enhanced chemical vapor deposition. Chemical Communications, 2006, , 2899.	2.2	30
99	High resolution structural characterization of the amorphousâ€crystalline interface in Se+â€implanted GaAs. Applied Physics Letters, 1984, 44, 874-876.	1.5	29
100	Ternary phases in the Pd-GaAs system: Implications for shallow contacts to GaAs. Materials Letters, 1985, 3, 409-413.	1.3	29
101	Magneto-transport in ultrathin ErAs epitaxial layers buried in GaAs. Surface Science, 1990, 228, 13-15.	0.8	28
102	Optical spectroscopy of GaN microcavities with thicknesses controlled using a plasma etchback. Applied Physics Letters, 2001, 79, 3029-3031.	1.5	28
103	Electrical properties of individual gold nanowires arrayed in a porous anodic alumina template. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3152-3158.	0.8	28
104	First-principles analysis of ZrN/ScN metal/semiconductor superlattices for thermoelectric energy conversion. Journal of Applied Physics, 2011, 109, .	1.1	28
105	High resolution transmission electron microscopy of protonâ€implanted gallium arsenide. Applied Physics Letters, 1985, 47, 691-693.	1.5	27
106	Effects of KrF excimer laser irradiation on metal contacts to n-type and p-type GaN. Journal of Applied Physics, 2003, 94, 3529-3535.	1.1	27
107	Thermal stability of epitaxial cubic-TiN/(Al,Sc)N metal/semiconductor superlattices. Journal of Materials Science, 2015, 50, 3200-3206.	1.7	27
108	In/GaAs reaction: Effect of an intervening oxide layer. Applied Physics Letters, 1986, 49, 818-820.	1.5	26

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109	Epitaxial metal(NiAl)-semiconductor(IIIâ€“V) heterostructures by MBE. Surface Science, 1990, 228, 1-8.	0.8	26
110	Simple Ru electrode scheme for ferroelectric (Pb,La)(Zr,Ti)O3 capacitors directly on silicon. Journal of Applied Physics, 1998, 84, 1121-1125.	1.1	26
111	III-nitride nanopyramid light emitting diodes grown by organometallic vapor phase epitaxy. Journal of Applied Physics, 2010, 108, 044303.	1.1	26
112	Magnetic Manipulation and Optical Imaging of an Active Plasmonic Single-Particle Feâ€“Au Nanorod. Langmuir, 2011, 27, 15292-15298.	1.6	25
113	Growth of TiNâˆ•GaN metal/semiconductor multilayers by reactive pulsed laser deposition. Journal of Applied Physics, 2006, 100, 064901.	1.1	24
114	Microstructural evolution and thermal stability of HfN/ScN, ZrN/ScN, and Hf0.5Zr0.5N/ScN metal/semiconductor superlattices. Journal of Materials Science, 2016, 51, 8250-8258.	1.7	24
115	Decoupling the structural and magnetic phase transformations in magneto-optic MnBi thin films by the partial substitution of Cr for Mn. Applied Physics Letters, 1998, 72, 2337-2339.	1.5	23
116	Epitaxial growth of semiconducting LaVO₃ thin films. Journal of Materials Research, 2000, 15, 1-3.	1.2	22
117	Toward surround gates on vertical single-walled carbon nanotube devices. Journal of Vacuum Science & Technology B, 2009, 27, 821.	1.3	22
118	Enhanced hardness in epitaxial TiAlScN alloy thin films and rocksalt TiN/(Al,Sc)N superlattices. Applied Physics Letters, 2014, 105, .	1.5	22
119	Tailoring of surface plasmon resonances in TiN/(Al0.72Sc0.28)N multilayers by dielectric layer thickness variation. Journal of Materials Science, 2018, 53, 4001-4009.	1.7	22
120	Optical properties of metallic quantum wells. IEEE Journal of Quantum Electronics, 1992, 28, 1663-1669.	1.0	21
121	In-place fabrication of nanowire electrode arrays for vertical nanoelectronics on Si substrates. Journal of Vacuum Science & Technology B, 2007, 25, 343.	1.3	21
122	Controlled Decoration of Single-Walled Carbon Nanotubes with Pd Nanocubes. Journal of Physical Chemistry C, 2007, 111, 13756-13762.	1.5	21
123	Thermoelectric properties of HfN/ScN metal/semiconductor superlattices: a first-principles study. Journal of Physics Condensed Matter, 2012, 24, 415303.	0.7	21
124	Backside secondary ion mass spectrometry study of a Ge/Pd ohmic contact to InP. Applied Physics Letters, 1992, 60, 1123-1125.	1.5	20
125	Fluence effects on the magnetic properties of Fe81B13.5Si3.5C2 metallic glass produced by pulsed laser deposition. Journal of Applied Physics, 1999, 85, 6652-6654.	1.1	20
126	Microfabrication using one-step LPCVD porous polysilicon films. Journal of Microelectromechanical Systems, 2003, 12, 418-424.	1.7	20

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127	Electrical properties of metal contacts on laser-irradiated n-type GaN. Applied Physics Letters, 2003, 82, 580-582.	1.5	20
128	Non-volatile memory characteristics of submicrometre Hall structures fabricated in epitaxial ferromagnetic MnAl films on GaAs. Electronics Letters, 1993, 29, 421.	0.5	19
129	Kinetics of the Pd/In thin-film bilayer reaction: Implications for transient-liquid-phase wafer bonding. Journal of Electronic Materials, 2001, 30, 1471-1475.	1.0	19
130	Modification of (Pb,La)(Zr,Ti)O3 thin films during pulsed laser liftoff from MgO substrates. Journal of Applied Physics, 2003, 94, 4047-4052.	1.1	19
131	Optimization of carbon nanotube synthesis from porous anodic Alâ€“Feâ€“Al templates. Carbon, 2007, 45, 2290-2296.	5.4	19
132	Independently addressable fields of porous anodic alumina embedded in SiO[sub 2] on Si. Applied Physics Letters, 2008, 92, 013122.	1.5	19
133	Capacitance-voltage modeling of metal-ferroelectric-semiconductor capacitors based on epitaxial oxide heterostructures. Applied Physics Letters, 2011, 98, 102901.	1.5	19
134	Crystallographic relationships between GaAs, As and Ga2O3 at the GaAs-thermal oxide interface. Materials Letters, 1985, 3, 247-250.	1.3	18
135	Electrical resistivity of thin epitaxial NiAl buried in (Al,Ga)As. Applied Physics Letters, 1989, 54, 2112-2114.	1.5	18
136	Chemical effects in ion mixing of a ternary system (metalâ€“SiO2). Applied Physics Letters, 1987, 50, 571-573.	1.5	17
137	The Si/Pd(Si,Ge) ohmic contact onnâ€“GaAs. Applied Physics Letters, 1992, 60, 3016-3018.	1.5	17
138	Organometallic vapor phase epitaxial growth of GaN on ZrNâˆ•AlNâˆ•Si substrates. Applied Physics Letters, 2008, 93, 023109.	1.5	17
139	Selectiveâ€area epitaxy of GaAs through silicon dioxide windows by molecular beam epitaxy. Applied Physics Letters, 1986, 48, 142-144.	1.5	16
140	Correlation between solidâ€state reaction and electrical properties of the Rh/GaAs Schottky contact. Journal of Applied Physics, 1987, 61, 1099-1102.	1.1	16
141	Magnetic and magnetoâ€optic properties of epitaxial ferromagnetic Ï„â€MnAl/(Al,Ga)As heterostructures. Applied Physics Letters, 1992, 60, 1393-1395.	1.5	16
142	High-Tc superconducting NbN films with low particulate density grown at 25 Â°C using pulsed laser deposition. Journal of Materials Research, 2001, 16, 1223-1226.	1.2	16
143	Cross-plane thermoelectric transport in p-type La0.67Sr0.33MnO3/LaMnO3 oxide metal/semiconductor superlattices. Journal of Applied Physics, 2013, 113, 193702.	1.1	16
144	Thin film Yî—¸Baî—¸Cuî—¸O high superconductors: structure-property relationships. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 14, 188-213.	1.7	15

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145	Self-supporting nanowire arrays templated in sacrificial branched porous anodic alumina for thermoelectric devices. Applied Physics Letters, 2009, 95, .	1.5	15
146	Pseudomorphic stabilization of rocksalt GaN in TiN/GaN multilayers and superlattices. Physical Review B, 2009, 80, .	1.1	15
147	Understanding the Rocksalt-to-Wurtzite phase transformation through microstructural analysis of (Al,Sc)N epitaxial thin films. Applied Physics Letters, 2016, 109, .	1.5	15
148	Interfacial interactions of evaporated iridium thin films with (100) GaAs. Journal of Applied Physics, 1987, 62, 1815-1820.	1.1	14
149	Thermomechanical and Thermal Contact Characteristics of Bismuth Telluride Films Electrodeposited on Carbon Nanotube Arrays. Advanced Materials, 2009, 21, 4280-4283.	11.1	14
150	Electrodeposition of InSb branched nanowires: Controlled growth with structurally tailored properties. Journal of Applied Physics, 2014, 116, 083506.	1.1	14
151	Epitaxial Ï„MnAl/NiAl magnetic multilayers on AlAs/GaAs. Applied Physics Letters, 1993, 63, 839-841.	1.5	13
152	Bimodal spatial distribution of pores in anodically oxidized aluminum thin films. Journal of Applied Physics, 2000, 88, 6875-6880.	1.1	13
153	Epitaxial growth of skutterudite (CoSb3) thin films on (001) InSb by pulsed laser deposition. Journal of Materials Research, 2001, 16, 2467-2470.	1.2	13
154	Templated synthesis of goldâ€“iron alloy nanoparticles using pulsed laser deposition. Nanotechnology, 2006, 17, 5131-5135.	1.3	13
155	Vertical Carbon Nanotube Devices With Nanoscale Lengths Controlled Without Lithography. IEEE Nanotechnology Magazine, 2009, 8, 469-476.	1.1	13
156	Built-in Electric Field Minimization in (In, Ga)N Nanoheterostructures. Nano Letters, 2011, 11, 4515-4519.	4.5	13
157	Cross-plane electronic and thermal transport properties of p-type La0.67Sr0.33MnO3/LaMnO3 perovskite oxide metal/semiconductor superlattices. Journal of Applied Physics, 2012, 112, 063714.	1.1	13
158	A nanocapacitor with giant dielectric permittivity. Nanotechnology, 2006, 17, 2284-2288.	1.3	12
159	Preparation and Optical Characterization of Sol-Gel Deposited Pb(Zr0.45Ti0.55)O3 Films. Journal of Sol-Gel Science and Technology, 2000, 19, 157-162.	1.1	11
160	Effect of KOH treatment on the schottky barrier height and reverse leakage current in Pt/n-GaN. Journal of Electronic Materials, 2006, 35, 107-112.	1.0	11
161	Linear Coefficient of Thermal Expansion of Porous Anodic Alumina Thin Films from Atomic Force Microscopy. Nanoscale and Microscale Thermophysical Engineering, 2009, 13, 243-252.	1.4	11
162	Void-mediated coherency-strain relaxation and impediment of cubic-to-hexagonal transformation in epitaxial metastable metal/semiconductor <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mi>TiN</mml:mi><mml:mtext>/</mml:mtext><mml:mathvariant="normal">A</mml:mi></mml:mrow><mml:msub><mml:mi mathvariant="normal">I</mml:mi><mml:mrow><mml:mn>0.72</mml:mn></mml:mrow></mml:msub><mml:mi mathvariant="normal">S</mml:mi><mml:msub><mml:mi mathvariant="normal">c</mml:mi><mml:mrow	0.9	11

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